

**GaAs-IR-Lumineszenzdiode in SMT-Gehäuse**  
**GaAs Infrared Emitter in SMT Package**  
**Lead (Pb) Free Product - RoHS Compliant**

**SFH 4211**



**Wesentliche Merkmale**

- GaAs-LED mit sehr hohem Wirkungsgrad
- Gute Linearität ( $I_e = f [I_F]$ ) bei hohen Strömen
- Gleichstrom- (mit Modulation) oder Impulsbetrieb möglich
- Hohe Zuverlässigkeit
- Hohe Impulsbelastbarkeit
- Oberflächenmontage geeignet
- Gegerartet lieferbar
- SFH 4211 Gehäusegleich mit SFH 320

**Features**

- Very highly efficient GaAs-LED
- Good Linearity ( $I_e = f [I_F]$ ) at high currents
- DC (with modulation) or pulsed operations are possible
- High reliability
- High pulse handling capability
- Suitable for surface mounting (SMT)
- Available on tape and reel
- SFH 4211 same package as SFH 320

**Anwendungen**

- Miniaturlichtschranken für Gleich- und Wechsellichtbetrieb, Lochstreifenleser
- Industrieelektronik
- „Messen/Steuern/Regeln“
- Automobiltechnik
- Sensorik
- Alarm- und Sicherungssysteme
- IR-Freiraumübertragung

**Applications**

- Miniature photointerrupters
- Industrial electronics
- For drive and control circuits
- Automotive technology
- Sensor technology
- Alarm and safety equipment
- IR free air transmission

Typ Type	Bestellnummer Ordering Code	Gehäuse Package
SFH 4211	Q65110A2515	Kathodenkennzeichnung: abgesetzte Ecke cathode marking: beveled edge TOPLED®

**Grenzwerte** ( $T_A = 25\text{ °C}$ )**Maximum Ratings**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 100	°C
Sperrspannung Reverse voltage	$V_R$	5	V
Durchlassstrom Forward current	$I_F$	100	mA
Stoßstrom, $\tau = 10\ \mu\text{s}$ , $D = 0$ Surge current	$I_{FSM}$	3	A
Verlustleistung Power dissipation	$P_{tot}$	160	mW
Wärmewiderstand Sperrschicht - Umgebung bei Montage auf FR4 Platine, Padgröße je $16\ \text{mm}^2$ Thermal resistance junction - ambient mounted on PC-board (FR4), pads size $16\ \text{mm}^2$ each	$R_{thJA}$	450	K/W
Wärmewiderstand Sperrschicht - Lötstelle bei Montage auf Metall-Block Thermal resistance junction - soldering point, mounted on metal block	$R_{thJS}$	200	K/W

**Kennwerte** ( $T_A = 25\text{ °C}$ )**Characteristics**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der Strahlung Wavelength at peak emission $I_F = 100\ \text{mA}$ , $t_p = 20\ \text{ms}$	$\lambda_{peak}$	950	nm
Spektrale Bandbreite bei 50% von $I_{max}$ Spectral bandwidth at 50% of $I_{max}$ $I_F = 100\ \text{mA}$	$\Delta\lambda$	55	nm
Abstrahlwinkel Half angle	$\varphi$	$\pm 60$	Grad deg.
Aktive Chipfläche Active chip area	$A$	0.09	$\text{mm}^2$
Abmessungen der aktiven Chipfläche Dimensions of the active chip area	$L \times B$ $L \times W$	$0.3 \times 0.3$	$\text{mm}^2$

Kennwerte ( $T_A = 25\text{ °C}$ )

Characteristics (cont'd)

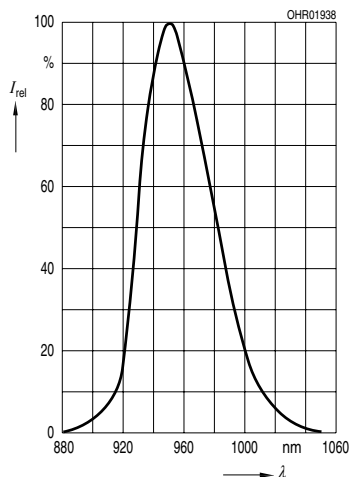
Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Schaltzeiten, $I_e$ von 10% auf 90% und von 90% auf 10%, bei $I_F = 100\text{ mA}$ , $R_L = 50\ \Omega$ Switching times, $I_e$ from 10% to 90% and from 90% to 10%, $I_F = 100\text{ mA}$ , $R_L = 50\ \Omega$	$t_r, t_f$	0.5	$\mu\text{s}$
Kapazität Capacitance $V_R = 0\text{ V}$ , $f = 1\text{ MHz}$	$C_o$	25	pF
Durchlassspannung Forward voltage $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$ $I_F = 1\text{ A}$ , $t_p = 100\ \mu\text{s}$	$V_F$ $V_F$	1.3 ( $\leq 1.5$ ) 2.3 ( $\leq 2.8$ )	V V
Sperrstrom Reverse current $V_R = 5\text{ V}$	$I_R$	0.01 ( $\leq 1$ )	$\mu\text{A}$
Gesamtstrahlungsfluss Total radiant flux $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$	$\Phi_e$	20	mW
Temperaturkoeffizient von $I_e$ bzw. $\Phi_e$ , $I_F = 100\text{ mA}$ Temperature coefficient of $I_e$ or $\Phi_e$ , $I_F = 100\text{ mA}$	$TC_I$	- 0.5	%/K
Temperaturkoeffizient von $V_F$ , $I_F = 100\text{ mA}$ Temperature coefficient of $V_F$ , $I_F = 100\text{ mA}$	$TC_V$	- 2	mV/K
Temperaturkoeffizient von $\lambda$ , $I_F = 100\text{ mA}$ Temperature coefficient of $\lambda$ , $I_F = 100\text{ mA}$	$TC_\lambda$	+ 0.3	nm/K

Strahlstärke  $I_e$  in Achsrichtung (gemessen bei einem Raumwinkel  $\Omega = 0.01\text{ sr}$ )Radiant Intensity  $I_e$  in Axial Direction (at a solid angle of  $\Omega = 0.01\text{ sr}$ )

Bezeichnung Parameter	Symbol	Werte Values	Einheit Unit
Strahlstärke Radiant intensity $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$	$I_{e\text{ min}}$ $I_{e\text{ typ}}$	2.5 6.0	mW/sr mw/sr
Strahlstärke Radiant intensity $I_F = 1\text{ A}$ , $t_p = 100\ \mu\text{s}$	$I_{e\text{ typ.}}$	45	mW/sr

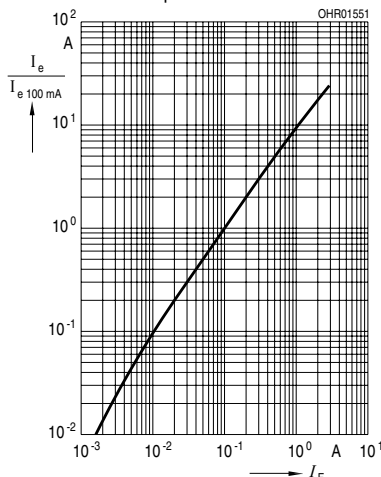
**Relative Spectral Emission**

$I_{rel} = f(\lambda)$

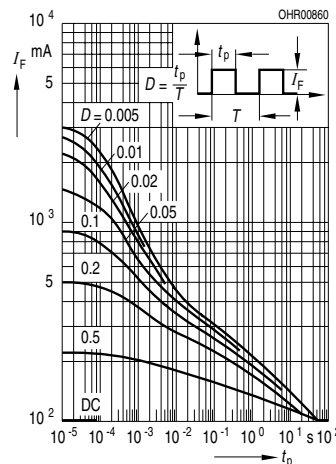


**Radiant Intensity**  $\frac{I_e}{I_e 100 \text{ mA}} = f(I_F)$

Single pulse,  $t_p = 20 \mu\text{s}$

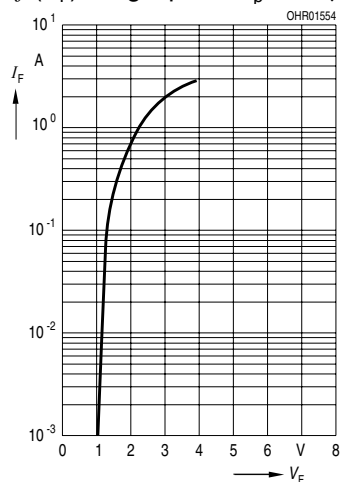


**Permissible Pulse Handling Capability**  $I_F = f(t_p)$ , duty cycle  $D =$  parameter,  $T_A = 20 \text{ }^\circ\text{C}$



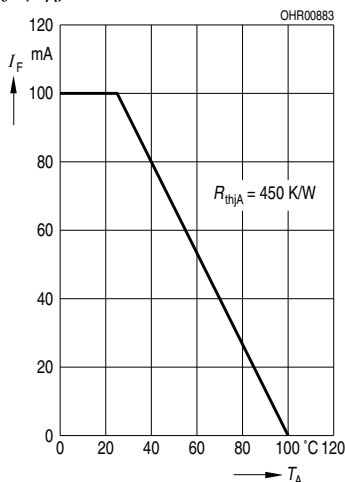
**Forward Current**

$I_F = f(V_F)$ , single pulse,  $t_p = 20 \mu\text{s}$



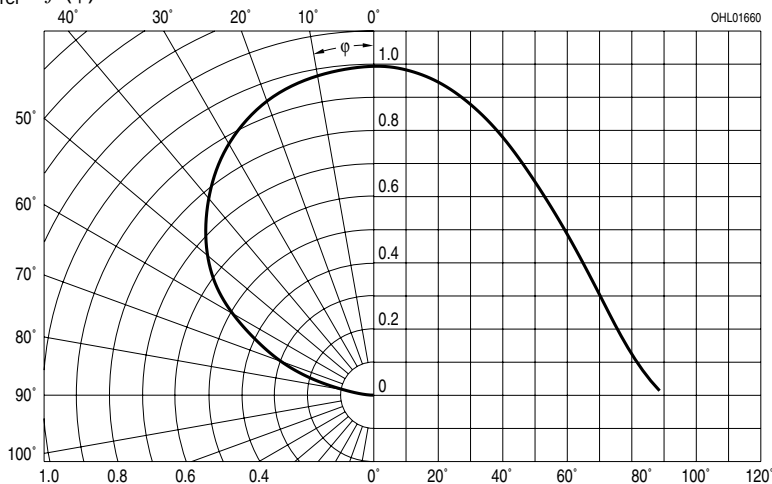
**Max. Permissible Forward Current**

$I_F = f(T_A)$

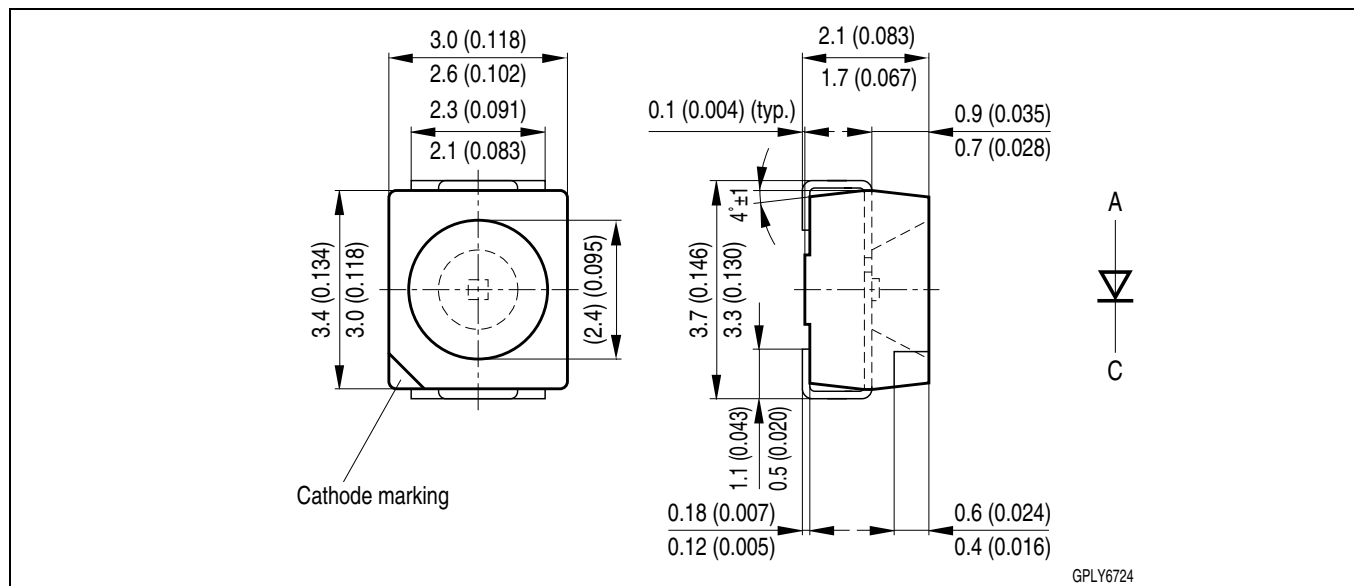


**Radiation Characteristics**

$S_{rel} = f(\varphi)$



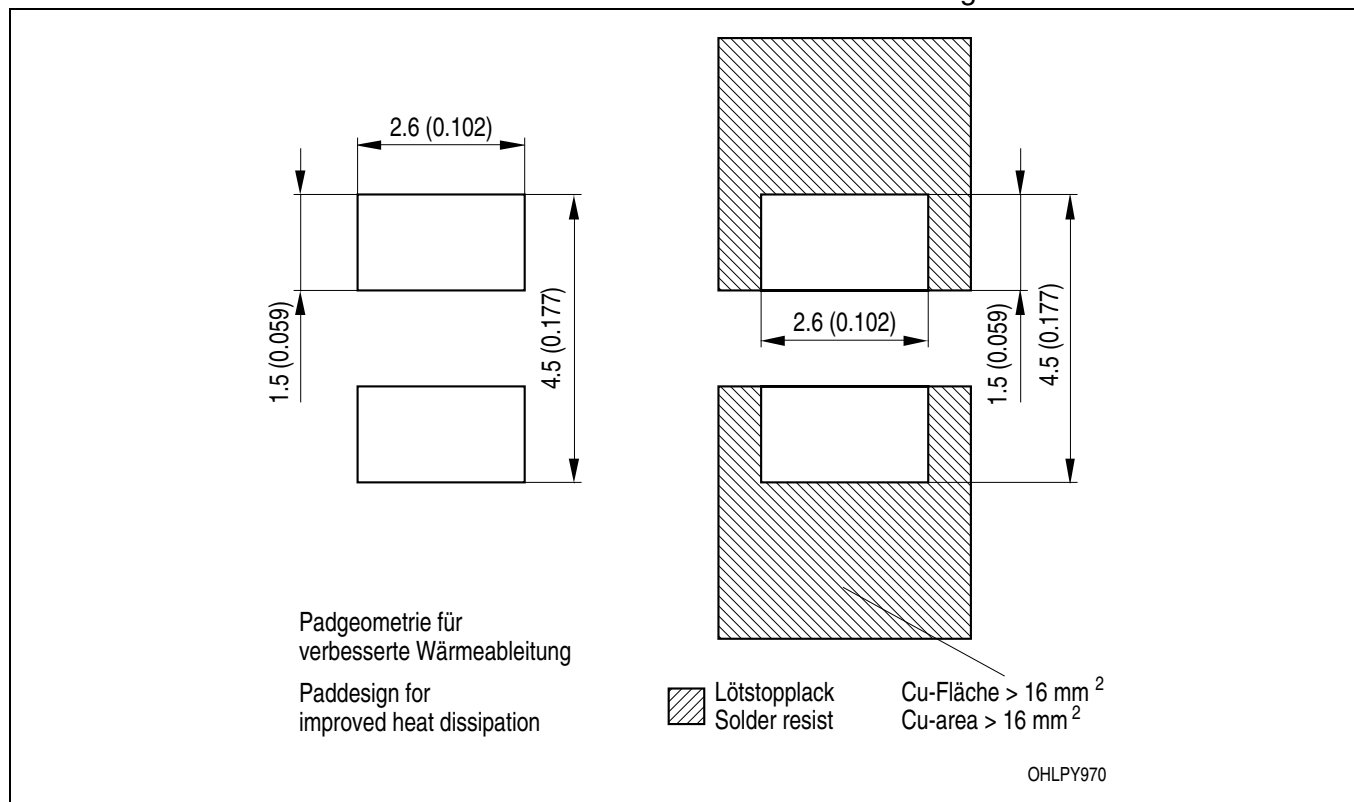
**Maßzeichnung  
Package Outlines**



Maße in mm (inch) / Dimensions in mm (inch).

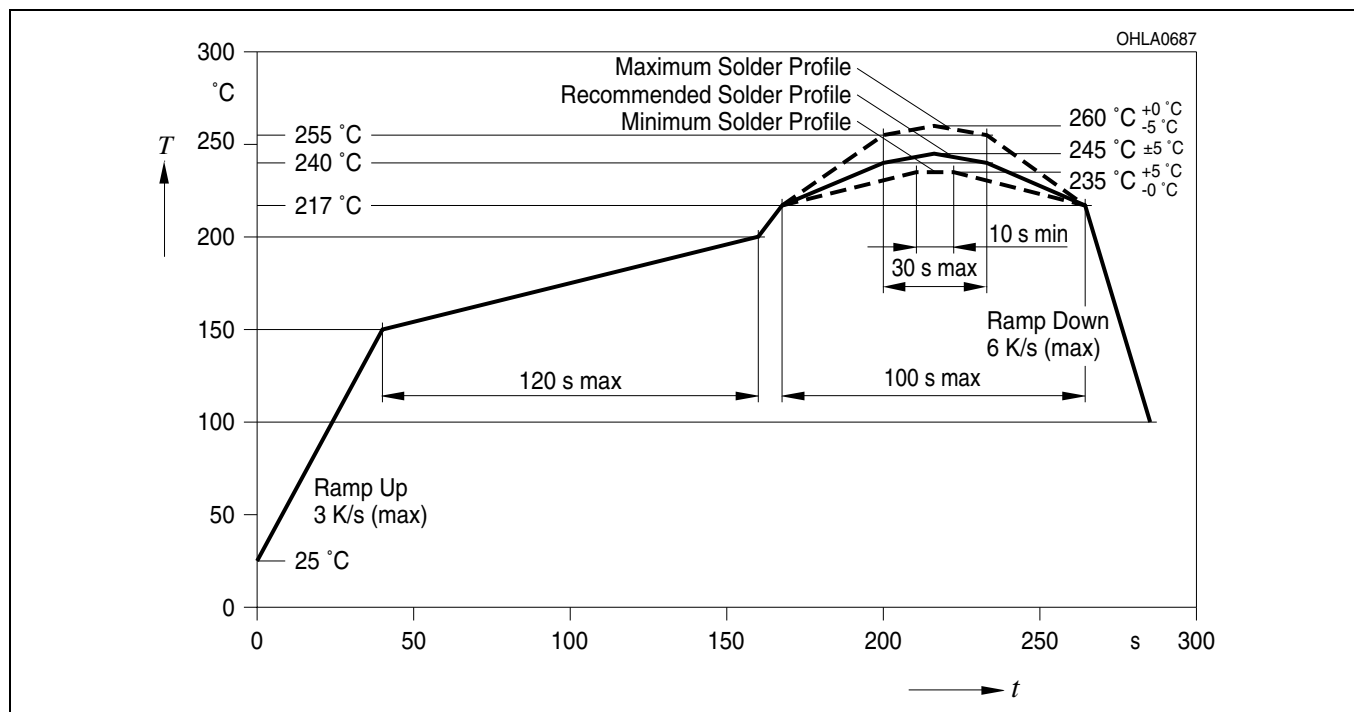
**Empfohlenes Lötpaddesign  
Recommended Solder Pad**

**Reflow Löten  
Reflow Soldering**



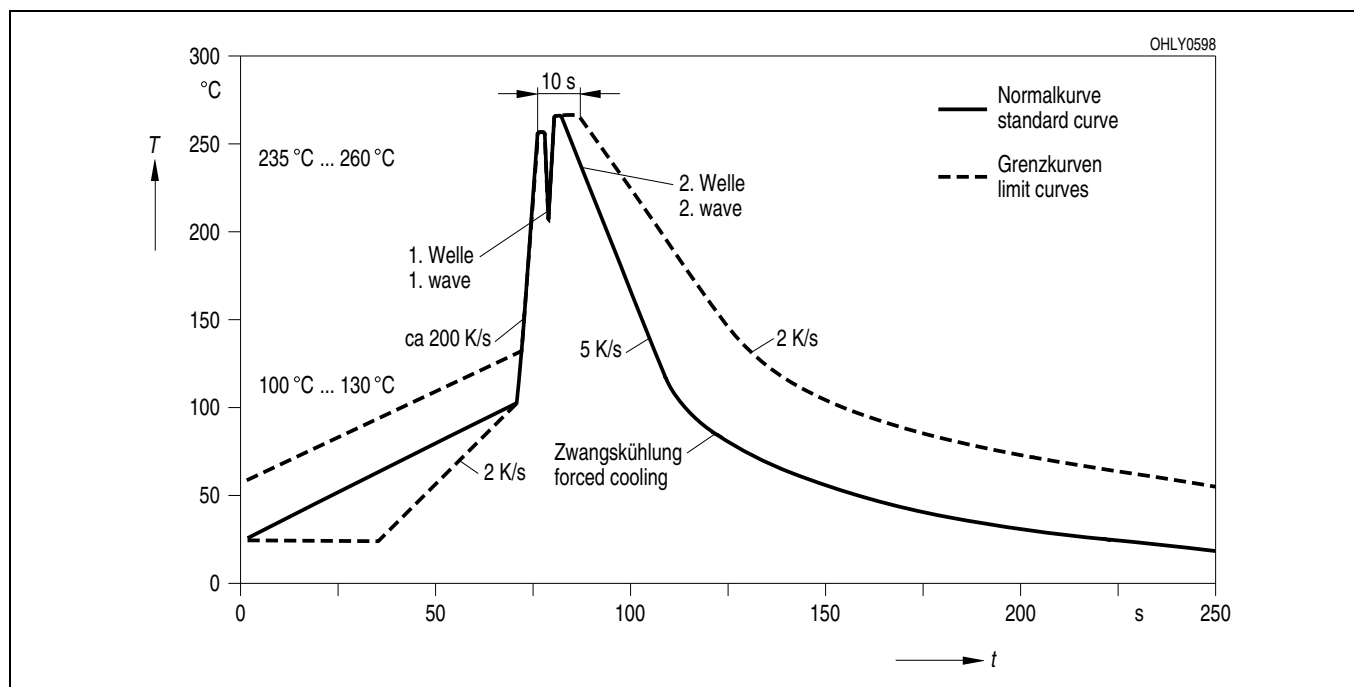
**Lötbedingungen**  
**Soldering Conditions**  
**Reflow Lötprofil für bleifreies Löten**  
**Reflow Soldering Profile for lead free soldering**

Vorbehandlung nach JEDEC Level 2  
 Preconditioning acc. to JEDEC Level 2  
 (nach J-STD-020C)  
 (acc. to J-STD-020C)



**Wellenlöten (TTW)**  
**TTW Soldering**

(nach CECC 00802)  
 (acc. to CECC 00802)



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